Single 2-Input NOR Gate with Open Drain Output

NLV74VHC1G03, NLV74VHC1GT03

The NLV74VHC1G03 / NLV74VHC1GT03 is a 2−input NOR Gate with an open drain output in tiny footprint packages.

The input structures provide protection when voltages up to 5.5 V are applied, regardless of the supply voltage. This allows the device to be used to interface 5 V circuits to 3 V circuits. Some output structures also provide protection when V_{CC} = 0 V and when the output voltage exceeds V_{CC}. These input and output structures help prevent device destruction caused by supply voltage − input/output voltage mismatch, battery backup, hot insertion, etc.

Features

- Designed for 2.0 V to 5.5 V V_{CC} Operation
- 3.5 ns t_{PD} at 5 V (typ)
- Inputs/Outputs Over−Voltage Tolerant up to 5.5 V
- I_{OFF} Supports Partial Power Down Protection
- Source/Sink 8 mA at 3.0 V
- Available in SC−88A and TSOP−5 Packages
- Chip Complexity < 100 FETs
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q100 Qualified and PPAP Capable
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

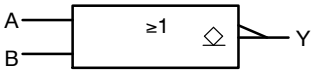
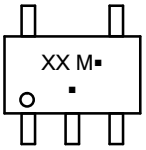


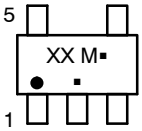
Figure 1. Logic Symbol

MARKING DIAGRAMS

SC−88A
DF SUFFIX
CASE 419A



TSOP−5
DT SUFFIX
CASE 483



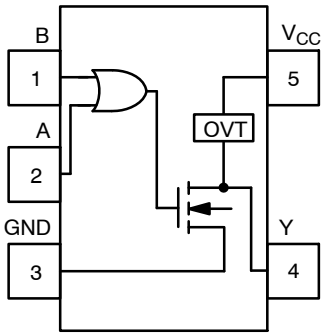
XX = Specific Device Code
M = Date Code*
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering, marking and shipping information on page 8 of this data sheet.



(SC−88A/TSOP−5)

Figure 2. Pinout (Top View)

PIN ASSIGNMENT
(SC−88A/TSOP−5)

Pin	Function
1	B
2	A
3	GND
4	Y
5	V_{CC}

FUNCTION TABLE

Input		Output
A	**B**	**Y**
L	L	Z
L	H	L
H	L	L
H	H	L

MAXIMUM RATINGS

Symbol	Characteristics			Value	Unit
V_{CC}	DC Supply Voltage			−0.5 to +7.0	V
V_{IN}	DC Input Voltage			−0.5 to +7.0	V
V_{OUT}	DC Output Voltage	1Gxx		−0.5 to V_{CC} + 0.5	V
		1GTxx	Active−Mode (High or Low State) Tri−State Mode (Note 1) Power−Down Mode (V_{CC} = 0 V)	−0.5 to V_{CC} + 0.5 −0.5 to +7.0 −0.5 to +7.0	
I_{IK}	DC Input Diode Current		V_{IN} < GND	−20	mA
I_{OK}	DC Output Diode Current	1Gxx	V_{OUT} > V_{CC}, V_{OUT} < GND	±20	mA
		1GTxx	V_{OUT} < GND	−20	
I_{OUT}	DC Output Source/Sink Current			±25	mA
I_{CC} or I_{GND}	DC Supply Current per Supply Pin or Ground Pin			±50	mA
T_{STG}	Storage Temperature Range			−65 to +150	°C
T_L	Lead Temperature, 1 mm from Case for 10 secs			260	°C
T_J	Junction Temperature Under Bias			+150	°C
θ_{JA}	Thermal Resistance (Note 2)		SC−88A TSOP−5	377 320	°C/W
P_D	Power Dissipation in Still Air		SC−88A TSOP−5	332 390	mW
MSL	Moisture Sensitivity			Level 1	−
F_R	Flammability Rating		Oxygen Index: 28 to 34	UL 94 V−0 @ 0.125 in	−
V_{ESD}	ESD Withstand Voltage (Note 3)		Human Body Model Charged Device Model	2000 1000	V
$I_{Latchup}$	Latchup Performance (Note 4)			±100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Applicable to devices with outputs that may be tri−stated.
2. Measured with minimum pad spacing on an FR4 board, using 10mm−by−1inch, 2 ounce copper trace no air flow per JESD51−7.
3. HBM tested to ANSI/ESDA/JEDEC JS−001−2017. CDM tested to EIA/JESD22−C101−F. JEDEC recommends that ESD qualification to EIA/JESD22−A115−A (Machine Model) be discontinued per JEDEC/JEP172A.
4. Tested to EIA/JESD78 Class II.

RECOMMENDED OPERATING CONDITIONS

Symbol	Characteristics		Min	Max	Unit
V_{CC}	Positive DC Supply Voltage		2.0	5.5	V
V_{IN}	DC Input Voltage		0	5.5	V
V_{OUT}	DC Output Voltage	1Gxx	0	V_{CC}	V
		1GTxx Active−Mode (High or Low State) Tri−State Mode (Note 1) Power−Down Mode (V_{CC} = 0 V)	0 0 0	V_{CC} 5.5 5.5	
T_A	Operating Temperature Range		−55	+125	°C
t_r , t_f	Input Rise and Fall Time V_{CC} = 3.0 V to 3.6 V V_{CC} = 4.5 V to 5.5 V		 0 0	 100 20	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS (NLV74VHC1G03)

Symbol	Parameter	Test Conditions	V_{CC} (V)	T_A = 25°C			−40°C ≤ T_A ≤ 85°C		−55°C ≤ T_A ≤ 125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
V_{IH}	High−Level Input Voltage		2.0	1.5	–	–	1.5	–	1.5	–	V
			3.0	2.1	–	–	2.1	–	2.1	–	
			4.5	3.15	–	–	3.15	–	3.15	–	
			5.5	3.85	–	–	3.85	–	3.85	–	
V_{IL}	Low−Level Input Voltage		2.0	–	–	0.5	–	0.5	–	0.5	V
			3.0	–	–	0.9	–	0.9	–	0.9	
			4.5	–	–	1.35	–	1.35	–	1.35	
			5.5	–	–	1.65	–	1.65	–	1.65	
V_{OL}	Low−Level Output Voltage	V_{IN} = V_{IH} or V_{IL}									V
		I_{OL} = 50 μA	2.0	–	0.0	0.1	–	0.1	–	0.1	
		I_{OL} = 50 μA	3.0	–	0.0	0.1	–	0.1	–	0.1	
		I_{OL} = 50 μA	4.5	–	0.0	0.1	–	0.1	–	0.1	
		I_{OL} = 4 mA	3.0	–	–	0.36	–	0.44	–	0.52	
		I_{OL} = 8 mA	4.5	–	–	0.36	–	0.44	–	0.52	
I_{IN}	Input Leakage Current	V_{IN} = 5.5 V or GND	2.0 to 5.5	–	–	±0.1	–	±1.0	–	±1.0	μA
I_{OZ}	3−State Output Leakage Current	V_{OUT} = 0 V to 5.5 V	5.5	–	–	±0.25	–	±2.5	–	±2.5	μA
I_{OFF}	Power Off Leakage Current	V_{IN} = 5.5 V	0.0	–	–	1.0	–	10	–	10	μA
I_{CC}	Quiescent Supply Current	V_{IN} = V_{CC} or GND	5.5	–	–	1.0	–	20	–	40	μA

DC ELECTRICAL CHARACTERISTICS (NLV74VHC1GT03)

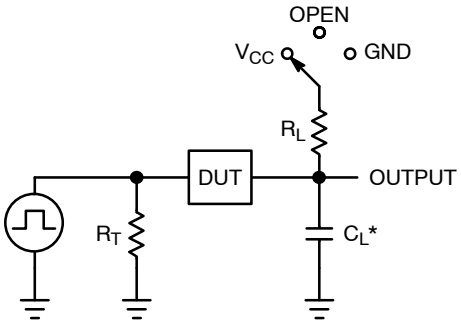
Symbol	Parameter	Test Conditions	V_{CC} (V)	T_A = 25°C			−40°C ≤ T_A ≤ 85°C		−55°C ≤ T_A ≤ 125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
V_{IH}	High−Level Input Voltage		2.0	1.0	–	–	1.0	–	1.0	–	V
			3.0	1.4	–	–	1.4	–	1.4	–	
			4.5	2.0	–	–	2.0	–	2.0	–	
			5.5	2.0	–	–	2.0	–	2.0	–	
V_{IL}	Low−Level Input Voltage		2.0	–	–	0.28	–	0.28	–	0.28	V
			3.0	–	–	0.45	–	0.45	–	0.45	
			4.5	–	–	0.8	–	0.8	–	0.8	
			5.5	–	–	0.8	–	0.8	–	0.8	
V_{OL}	Low−Level Output Voltage	V_{IN} = V_{IH} or V_{IL}									V
		I_{OL} = 50 μA	2.0	–	0.0	0.1	–	0.1	–	0.1	
		I_{OL} = 50 μA	3.0	–	0.0	0.1	–	0.1	–	0.1	
		I_{OL} = 50 μA	4.5	–	0.0	0.1	–	0.1	–	0.1	
		I_{OL} = 4 mA	3.0	–	–	0.36	–	0.44	–	0.52	
		I_{OL} = 8 mA	4.5	–	–	0.36	–	0.44	–	0.52	
I_{IN}	Input Leakage Current	V_{IN} = 5.5 V or GND	2.0 to 5.5	–	–	±0.1	–	±1.0	–	±1.0	μA
I_{OZ}	3−State Output Leakage Current	V_{OUT} = 0 V to 5.5 V	5.5	–	–	±0.25	–	±2.5	–	±2.5	μA
I_{OFF}	Power Off Leakage Current	V_{IN} = 5.5 V or V_{OUT} = 5.5 V	0	–	–	1.0	–	10	–	10	μA
I_{CC}	Quiescent Supply Current	V_{IN} = V_{CC} or GND	5.5	–	–	1.0	–	20	–	40	μA
I_{CCT}	Increase in Quiescent Supply Current per Input Pin	One Input: V_{IN} = 3.4 V; Other Input at V_{CC} or GND	5.5	–	–	1.35	–	1.5	–	1.65	mA

AC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Conditions	V_{CC} (V)	T_A = 25°C			−40°C ≤ T_A ≤ 85°C		−55°C ≤ T_A ≤ 125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
t_{PZL}	Propagation Delay, (A or B) to Y (Figures 3 and 4)	C_L = 15 pF	3.0 to 3.6	–	5.6	7.9	–	9.5	–	11.0	ns
		C_L = 50 pF		–	8.1	11.4	–	13.0	–	15.5	
		C_L = 15 pF	4.5 to 5.5	–	3.6	5.5	–	6.5	–	8.0	
		C_L = 50 pF		–	5.1	7.5	–	8.5	–	10.0	
t_{PLZ}	Propagation Delay, (A or B) to Y (Figures 3 and 4)	C_L = 15 pF	3.0 to 3.6	–	6.5	9.7	–	11.5	–	14.5	ns
		C_L = 50 pF		–	8.1	11.4	–	13.0	–	15.5	
		C_L = 15 pF	4.5 to 5.5	–	4.8	6.8	–	8.0	–	10.0	
		C_L = 50 pF		–	5.1	7.5	–	8.5	–	10.0	
C_{IN}	Input Capacitance			–	4.0	10	–	10	–	10	pF
C_{OUT}	Output Capacitance	Output in High Impedance State		–	6.0	–	–	–	–	–	pF

		Typical @ 25°C, V_{CC} = 5.0 V	
C_{PD}	Power Dissipation Capacitance (Note 5)	8.0	pF

5. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}$. C_{PD} is used to determine the no−load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.



C_L includes probe and jig capacitance
R_T is Z_{OUT} of pulse generator (typically 50 Ω)
f = 1 MHz

Test	Switch Position	C_L, pF	R_L, Ω
t_{PLH} / t_{PHL}	Open	See AC Characteristics Table	X
t_{PLZ} / t_{PZL}	V_{CC}		1 k
t_{PHZ} / t_{PZH}	GND		1 k

X = Don't Care

Figure 3. Test Circuit

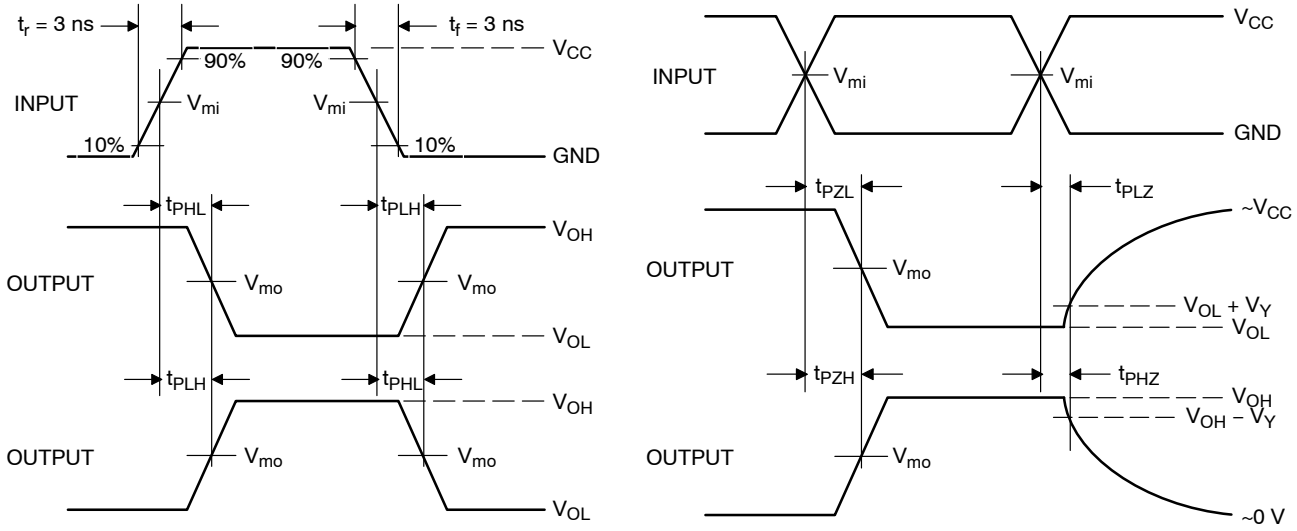


Figure 4. Switching Waveforms

V_{CC}, V	V_{mi}, V	V_{mo}, V		V_Y, V
		t_{PLH}, t_{PHL}	t_{PZL}, t_{PLZ}, t_{PZH}, t_{PHZ}	
3.0 to 3.6	V_{CC}/2	V_{CC}/2	V_{CC}/2	0.3
4.5 to 5.5	V_{CC}/2	V_{CC}/2	V_{CC}/2	0.3

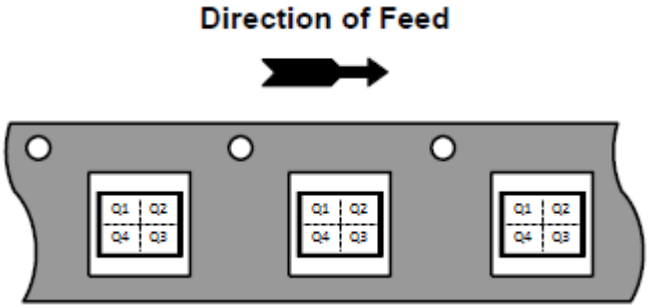
ORDERING INFORMATION

Device	Packages	Specific Device Code	Pin 1 Orientation (See below)	Shipping†
MC74VHC1G03DFT2G−L22038	SC−88A	VP	Q4	3000 / Tape & Reel
NLVVHC1G03DFT1G*	SC−88A	VP	Q2	3000 / Tape & Reel
MC74VHC1G03DTT1G	TSOP−5	VP	Q4	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q100 Qualified and PPAP Capable.

PIN 1 ORIENTATION IN TAPE AND REEL

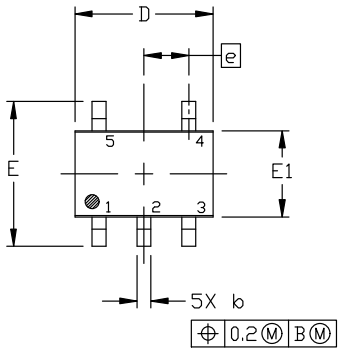


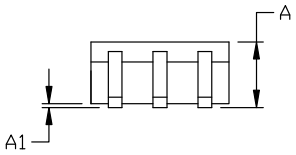
MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

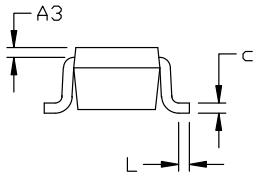
SCALE 2:1

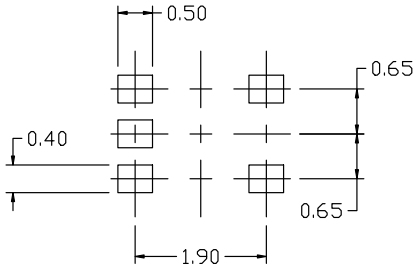
SC−88A (SC−70−5/SOT−353)
CASE 419A−02
ISSUE M

DATE 11 APR 2023









RECOMMENDED
MOUNTING FOOTPRINT

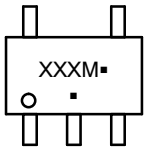
* For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS
3. 419A−01 OBSOLETE. NEW STANDARD 419A−02
4. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.1016MM PER SIDE.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.80	0.95	1.10
A1	---	---	0.10
A3	0.20 REF		
b	0.10	0.20	0.30
c	0.10	---	0.25
D	1.80	2.00	2.20
E	2.00	2.10	2.20
E1	1.15	1.25	1.35
e	0.65 BSC		
L	0.10	0.15	0.30

GENERIC MARKING DIAGRAM*



*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

XXX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

(Note: Microdot may be in either location)

STYLE 1:
PIN 1. BASE
2. EMITTER
3. BASE
4. COLLECTOR
5. COLLECTOR

STYLE 2:
PIN 1. ANODE
2. EMITTER
3. BASE
4. COLLECTOR
5. CATHODE

STYLE 3:
PIN 1. ANODE 1
2. N/C
3. ANODE 2
4. CATHODE 2
5. CATHODE 1

STYLE 4:
PIN 1. SOURCE 1
2. DRAIN 1/2
3. SOURCE 1
4. GATE 1
5. GATE 2

STYLE 5:
PIN 1. CATHODE
2. COMMON ANODE
3. CATHODE 2
4. CATHODE 3
5. CATHODE 4

STYLE 6:
PIN 1. EMITTER 2
2. BASE 2
3. EMITTER 1
4. COLLECTOR
5. COLLECTOR 2/BASE 1

STYLE 7:
PIN 1. BASE
2. EMITTER
3. BASE
4. COLLECTOR
5. COLLECTOR

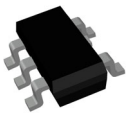
STYLE 8:
PIN 1. CATHODE
2. COLLECTOR
3. N/C
4. BASE
5. EMITTER

STYLE 9:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. ANODE
5. ANODE

Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

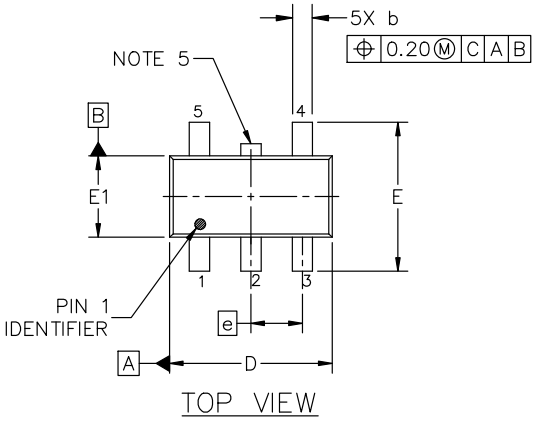
DOCUMENT NUMBER:	98ASB42984B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red.
DESCRIPTION:	SC−88A (SC−70−5/SOT−353)	PAGE 1 OF 1

MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

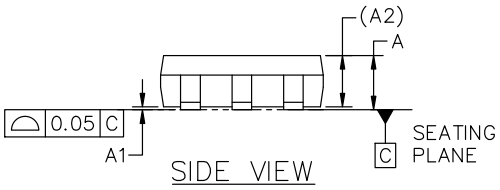


TSOP−5 3.00x1.50x0.95, 0.95P
CASE 483
ISSUE P

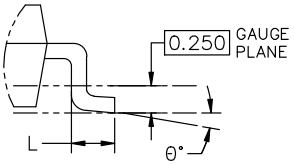
DATE 01 APR 2024



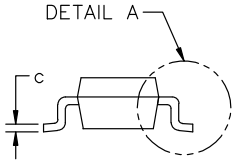
TOP VIEW



SIDE VIEW



DETAIL "A"
SCALE 2:1

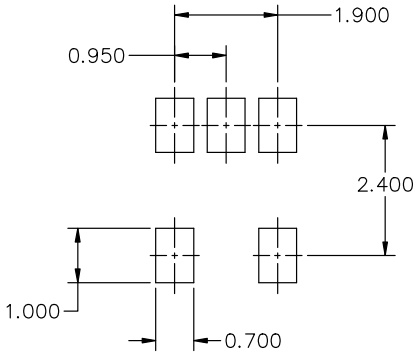


END VIEW

NOTES:

1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5−2018.
2. ALL DIMENSION ARE IN MILLIMETERS (ANGLES IN DEGREES).
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OF GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSION D.
5. OPTIONAL CONSTRUCTION: AN ADDITIONAL TRIMMED LEAD IS ALLOWED IN THIS LOCATION. TRIMMED LEAD NOT TO EXTEND MORE THAN 0.2 FROM BODY.

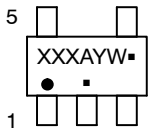
DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.900	1.000	1.100
A1	0.010	0.055	0.100
A2		0.950 REF.	
b	0.250	0.375	0.500
c	0.100	0.180	0.260
D	2.850	3.000	3.150
E	2.500	2.750	3.000
E1	1.350	1.500	1.650
e		0.950 BSC	
L	0.200	0.400	0.600
θ	0°	5°	10°



RECOMMENDED MOUNTING FOOTPRINT*

* FOR ADDITIONAL INFORMATION ON OUR Pb−FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

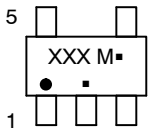
GENERIC
MARKING DIAGRAM*



Analog

XXX = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
▪ = Pb−Free Package

(Note: Microdot may be in either location)



Discrete/Logic

XXX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

DOCUMENT NUMBER:	**98ARB18753C**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	**TSOP−5 3.00x1.50x0.95, 0.95P**	**PAGE 1 OF 1**

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:
Technical Library: www.onsemi.com/design/resources/technical−documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support
For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales